PATENT ABSTRACTS OF JAPAN

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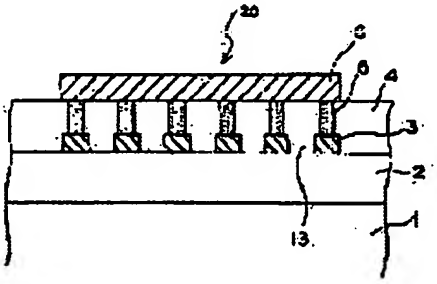
(54) SEMICONDUCTOR DEVICE AND BONDING PAD STRUCTURE THEREOF

(57)Abstract:
PURPOSE: To obtain a multilayer wiring structure having high reliability without crack at an interlayer insulating film at the time of wire bonding by providing a slit at a first wiring layer, filling a slit in the interlayer insulating layer, and providing a viahole.
CONSTITUTION: In a semiconductor device having a bonding pad 20 of a multilayer wiring structure which has at least first, second wiring layers 3, 6 and an interlayer insulating layer 4 having a viahole 5, the layer 3 has a wiring pattern which has a slit 13. The layer 4 is disposed at the upper side of the layer 3, and filled with slit 13, and the viahole 5 included in the layer 4 is disposed on the layer 3. Further, the layer 6 is formed on the upper side of the layer 4, electrically connected to the layer 3 via the viahole 5 and operated as a pad electrode for electrically inputting or outputting with the exterior of the device.



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